

IGBT

DIODE

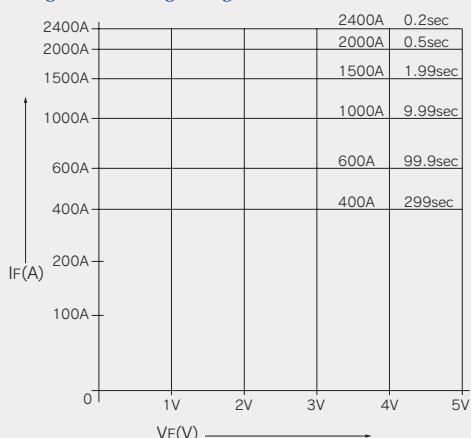
## SAFETY OPERATING AREA TEST SYSTEM 半導体安全動作領域テストシステム

# DDVF024ZZ 2400A



- DDVF024ZZ has been designed to test thermal resistance measurement with 2400A forcing power by resistance measurement of diodes and VCEON voltage of IGBT. By taking in optional temperature chamber to the system, it is possible to control temperature, calculate temperature coefficient, test thermal resistance measurement with certain surroundings temperature.
- ダイオードの熱抵抗測定とIGBTのVCEON電圧を用いて熱抵抗測定を行い、2400Aまでの印加パワーを持っています。オプションの恒温槽をシステムに組み込むことにより、恒温槽の温度を自由に管理できるため、温度係数を求めたり、一定の周囲温度での熱抵抗測定を可能とします。

**Forcing Power Range Diagram**



MODEL	DDVF024ZZ
MEASUREMENT RANGE	
PRE-TEST	B-E OPEN/SHORT VF1/VP1/VP2 0000mV~8191mV $\Delta VF$ 0000mV~1999mV
SETTING RANGE	
MEASURABLE DEVICES	DIODE, IGBT
IF	1A~2400A
IM	1mA~999mA
VG	0.1V~20.0V
POWER FORCING TIME(PT)	100 $\mu$ s~300s
DELAY TIME(DT)	10 $\mu$ s~999ms
LOWER GATE(LG)/UPPER GATE(UG)	0000mV~1999mV
BINNING AND INTERFACE	
OPEN/SHORT CHECK	VF1>4V…OPEN VF1<0.2V…SHORT
BIN INDICATION	PASS, LOW, HIGH, AVAL, REJECT
DIMENSIONS & WEIGHT	
MAIN UNIT	550(W)×1060+395(D)×1700(H)…190kg
IF UNIT	550(W)×1060(D)×1700(H)…500kg